Atty. Dkt. APPM/6551/CMI/TICL/RKK

ED STATES PATENT AND TRADEMARK OFFICE

๛๛๛๛๛๛๛๛๛๛

11

In re Application of:

Hytros, et al.

Serial No.: 10/033,544

Confirmation No.: 7363

Filed:

December 27, 2001

For:

Dual-Gas Delivery System

for Chemical Vapor **Deposition Processes**

Commissioner for Patents Washington, D.C. 20231

Dear Sir:

Group Art Unit:

Examiner:

to be assigned

CERTIFICATE OF MAILING

37 CFR 1.8

I hereby certify that this correspondence is being deposited on April 18, 2002 with the United States Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

The Applicants, and the Attorney who signs below on the basis of the information supplied by the inventor and the information in his file, submit herewith patents, publications, or other information of which they are aware, which may be material to the examination of this application and in respect of which there may be a duty to disclose in accordance with 37 CFR § 1.56.

While the information submitted in this Information Disclosure Statement may be material pursuant to 37 CFR § 1.56, it is not intended to constitute an admission that any patent, publication, or other information referred to therein is prior art for this invention unless specifically designated as such.

In accordance with 37 CFR § 1.97, this Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possibly material information as defined under 37 CFR § 1.56(a) exists.

The patents and/or publications submitted herewith are set forth on the attached Form PTO-1449.

Applicant believes that no fee is due as a result of this filing. However, If the Commissioner deems that fees are due under 37 CFR § 1.17(p) pursuant to § 1.97, he is hereby authorized to charge this fee, and any other fee necessary to make this submission timely, to Deposit Account No. 20-0782/AMAT 6551/CMI/TICL/RKK.

Respectfully submitted,

B. Todd Patterson

Registration No. 37,906

MOSER, PATTERSON & SHERIDAN, L.L.P.

3040 Post Oak Blvd., Suite 1500

Houston, TX 77056

Telephone: (713) 623-4844 Facsimile: (713) 623-4846 Attorney for Applicant(s)

Sheet 1 of 1 sheet(s) Docket No. Serial No. U.S. Department of Commerce, Patent and Trademark Office (PTO Form 1449 modified) AMAT/6551/CMI/TICL/ 10/033,544 RKK INFORMATION DISCLOSURE STATEMENT APPLICATION Applicant Confirmation No.: Hytros, et al. 7363 (Use several sheets if necessary) Filing Date Group December 27, 2001 Unknown **U.S. Patent Documents** Filing Date If Applicant(s) Class Subclass Document Issue *Examiner Number Date Name Appropriate Initial 438 238 02/12/1999 **A1** 6,200,844 03/13/2001 Huang 715 **A2** 6,148,761 11/21/2000 Majewski et al. 118 12/09/1998 **A3** 6,086,677 07/11/2000 Umotoy et al. 118 715 06/16/1998 Α4 10/19/1999 Shue et al. 438 656 07/23/1997 5,970,378 Α5 09/21/1999 Zenke 438 398 07/15/1997 5,956,595 02/16/1999 Crawley et al. 118 715 04/09/1997 **A6** 5,871,586 **A7** 5,665,640 09/09/1997 Foster et al. 438 680 06/03/1994 Α8 11/19/1996 Sandhu 427 534 11/08/1994 5,576,071 427 535 06/05/1995 A9 5,567,483 10/22/1996 Foster et al. 248.1 02/10/1992 A10 05/03/1994 Eichman et al. 427 5,308,655 Eichman et al. 427 255 08/16/1991 5,279,857 01/18/1994 A11 F reign Patent Documents Country Class **Subclass** Translation Date *Examiner Document Number Initial YES NO JΡ H01L 12/28 **B1** 63-22984 09/26/1988 C23C П EP 16/34 B2 0711846 05/15/1996

OTHER AF	`	- _T	
*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.	
	C1	Arena, et al., "A New Low Temperature PECVD TiN VMIC Conference, pp. 566-71, June 18-20, 1996	Compatible With Multilevel Vias Application",
	C2	Allendorf, et al., "Chemical Vapor Deposition", Proceedings of the Fourteenth International Conference and EUROCVD-11, Vol. 97-25, pp. 1625-33.	
	СЗ	Konecni, et al., "A Stable Plasma Treated CVD Titanium Nitride Film for Barrier/Glue Layer Applications", VMIC Conference, pp. 181-3.	
	C4	Kim, et al., "Effect of N ₂ /H _x Plasma Treatment on the Properties of TiN Films Prepared by Chemical Vapor Deposition from TiCl4 and NH ₃ ", Jap. J. Appl. Phys., Vol. 38, Part 2, No. 4B, pp. L461-3, April 15, 1999	
	C5	USSN 09/978,140, Zhang, et al., "Method of Titanium and Titanium Nitride Layer Deposition, filed October 15, 2001	
Examiner			Date Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.